

FEATURES

- 0.5 dB Minimum Noise Figure at 12 GHz
- 10 dB Associated Gain at 12 GHz
- 16.0 dBm P1dB at 12 GHz
- 0.15 Micron x 180 Micron Gate

APPLICATIONS

- Excellent Choice for Super Low Noise Applications
- Ideal for Commercial, Military, Hi-Rel Space Applications

DESCRIPTION

The MwT-LN180 is a super low noise, quasi-enhancement-mode pHEMT whose nominal 0.15 micron gate length and 180 micron gate width makes it ideally suited for applications requiring very low noise applications up to 30 GHz frequency. The device is equally effective for wideband (e.g. 6 to 18 GHz) and narrow-band applications. Each wafer can be screened to meet the high quality and reliability requirements for military and space applications.

RF SPECIFICATIONS AT Ta = 25 C

SYMBOL	PARAMETERS & CONDITIONS	FREQ	UNITS	MIN	TYP	MAX
NF min	Minimum Noise Figure Vds=2.5V Ids = 14 mA (Vgs=0)	4 GHz	dB		0.2	
		12 GHz			0.5	
SSG	Associated Gain Vds=2.5 V Ids = 14 mA (Vgs=0)	4 GHz	dB		14.5	
		12 GHz			10.0	
P1dB	Output Power at 1dB Compression Vds=3.0 V Ids = 50 mA	12 GHz	dBm		16.0	

Note: MwT-LN180 is a quasi enhancement mode device. For best noise figure, Vgs bias voltage should be set at either 0 or slightly positive voltages to achieve the target operating current.

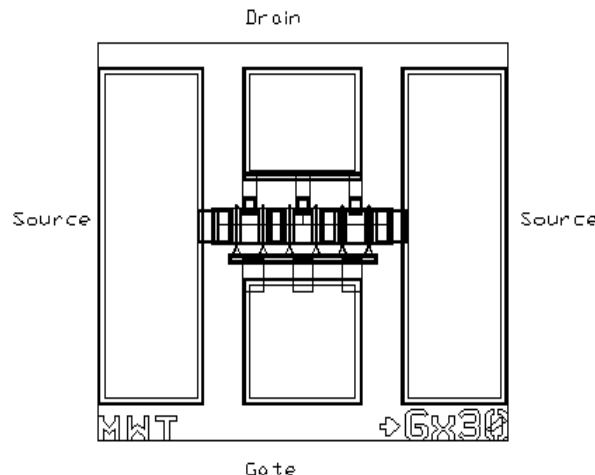
DC SPECIFICATIONS AT Ta = 25 C

SYMBOL	PARAMETERS & CONDITIONS	FREQ	UNITS	MIN	TYP	MAX
Imax	Saturated Drain Current Vds = 2.5V Vgs = 0.6V		mA		70	
Gm	Transconductance Vds = 2.5V Vgs = 0.2V		mS	140	180	
Vp	Pinch-off Voltage Vds = 2.0V Ids = 0.5mA		V		-0.2	
BVGSO	Gate-to-Source Breakdown Voltage Igs = -0.3mA		V	-6.0	-8.0	
BVGDO	Gate-to-Drain Breakdown Voltage Igd = -0.3mA		V	-7.5	-9.0	
Rth *	Chip Thermal Resistance		°C/W		300	

* Overall Rth depends on chip mounting

NOISE PARAMETERS Vds=2.5V, Ids=14mA

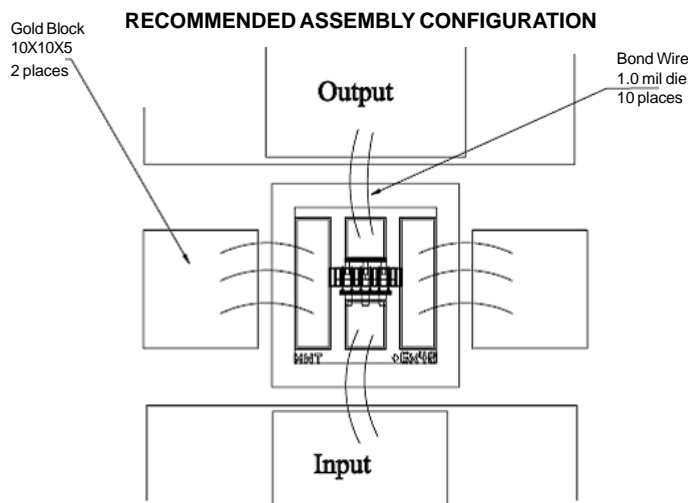
Freq (GHz)	NFmin (dB)	GA (dB)	Gamma Opt		Rn/50
			Mag	Ang	
2	0.17	18	0.73	-3.7	0.17
4	0.20	15	0.806	11.6	0.18
6	0.26	11.8	0.841	26.4	0.19
8	0.35	10.5	0.841	40.8	0.18
10	0.43	10	0.815	54.4	0.17
12	0.52	10	0.769	67.2	0.16
14	0.61	10	0.712	79.1	0.15
16	0.69	9.8	0.652	89.9	0.14
18	0.78	9.5	0.595	99.5	0.13
20	0.86	9.1	0.549	107.8	0.12
22	0.95	8.5	0.523	114.6	0.12
24	1.03	8	0.523	119.8	0.12
26	1.12	7.2	0.558	123.3	0.13



Chip Dimensions: 410 x 430 microns
Source pad: 80 x 280
Gate and Drain pad: 90 x 90
Chip Thickness: 100 microns

S-PARAMETERS V=2.5V, Ids=14mA

F [GHz]	S11		S21		S12		S22		K	GMAX dB
	Mag	Ang	Mag	Ang	Mag	Ang	Mag	Ang		
1	0.97	-16.8	8.44	165.9	0.024	77.2	0.58	-11.8	0.20	25.5
2	0.95	-32.7	8.06	157.2	0.046	70.8	0.57	-26.2	0.11	22.4
3	0.93	-47.3	7.59	148.5	0.066	61.6	0.55	-38.8	0.12	20.6
4	0.91	-60.4	7.08	140.4	0.082	55.0	0.54	-50.0	0.11	19.4
5	0.89	-72.5	6.55	133.1	0.095	48.1	0.51	-60.5	0.11	18.4
6	0.87	-82.5	6.06	126.9	0.105	42.2	0.50	-69.0	0.13	17.6
7	0.86	-91.7	5.60	121.1	0.114	37.2	0.48	-77.1	0.13	16.9
8	0.85	-100.1	5.20	115.8	0.122	32.7	0.47	-84.3	0.14	16.3
9	0.84	-107.0	4.83	111.1	0.126	29.0	0.46	-90.3	0.14	15.8
10	0.83	-113.4	4.48	106.8	0.130	25.2	0.45	-96.3	0.16	15.4
11	0.82	-118.8	4.17	102.9	0.134	22.0	0.43	-100.8	0.18	14.9
12	0.80	-123.3	3.90	99.5	0.136	19.2	0.43	-104.9	0.21	14.6
13	0.80	-127.7	3.65	96.0	0.137	16.4	0.42	-108.6	0.21	14.2
14	0.79	-131.5	3.44	93.0	0.141	14.1	0.42	-112.5	0.23	13.9
15	0.80	-135.6	3.24	89.9	0.142	11.9	0.42	-116.0	0.23	13.6
16	0.79	-139.1	3.06	87.1	0.141	8.5	0.42	-118.8	0.24	13.4
17	0.79	-141.9	2.89	84.3	0.140	7.7	0.41	-121.5	0.27	13.2
18	0.77	-145.0	2.74	81.9	0.141	5.6	0.41	-123.6	0.32	12.9
19	0.77	-147.8	2.60	79.3	0.142	3.8	0.41	-126.1	0.33	12.6
20	0.78	-149.7	2.47	77.0	0.145	3.2	0.40	-128.4	0.34	12.3
21	0.77	-151.8	2.36	74.9	0.143	-0.6	0.40	-129.4	0.37	12.2
22	0.76	-153.8	2.25	72.4	0.144	-1.7	0.40	-131.2	0.41	12.0
23	0.76	-155.5	2.15	70.7	0.142	-2.5	0.40	-132.4	0.42	11.8
24	0.76	-156.5	2.07	68.8	0.139	-4.9	0.40	-134.2	0.44	11.7
25	0.75	-159.8	1.97	66.8	0.140	-7.2	0.40	-135.4	0.51	11.5
26	0.75	-160.6	1.90	64.9	0.146	-5.9	0.40	-136.2	0.51	11.1



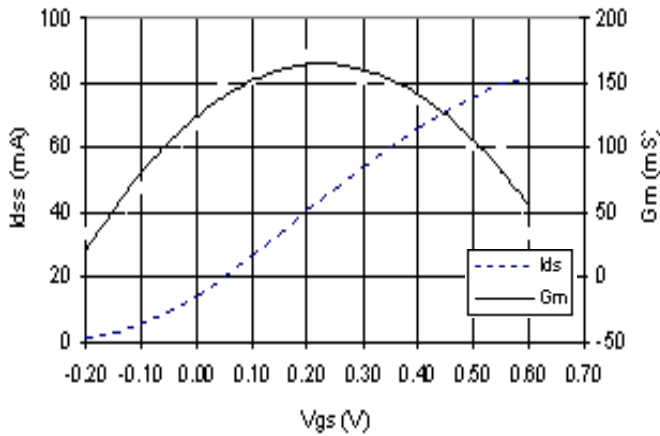
Note: The gold blocks and circuits should be placed as close to the device as possible. The bond wire should be as short as possible.

MAXIMUM RATINGS at Ta = 25 C

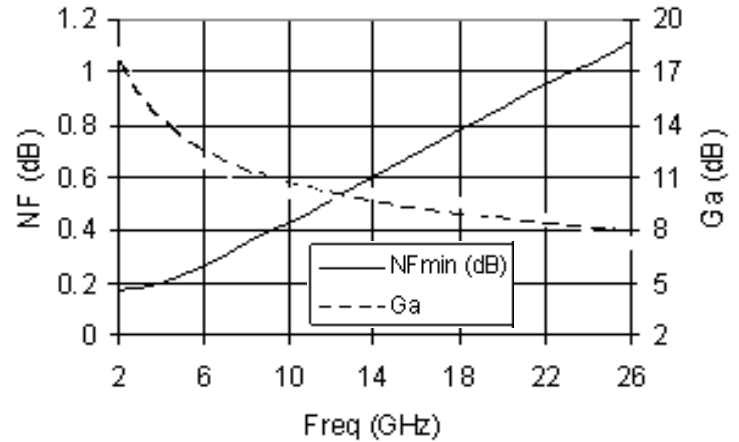
Symbol	Parameters	Units	Cont Max 1	Absolute Max 2
VDS	Drain to Source Voltage	V	4.0	4.5
Tch	Channel Temperature	°C	+150	+175
Tst	Storage Temperature	°C	-65 to +160	+180
Pin	RF Input Power	mW	10	20
Pt	Total Power Dissipation	mW	100	150

Exceeding any on of these limits in continuous operation may reduce the mean-time-to-failure below the design goal and may cause permanent damage

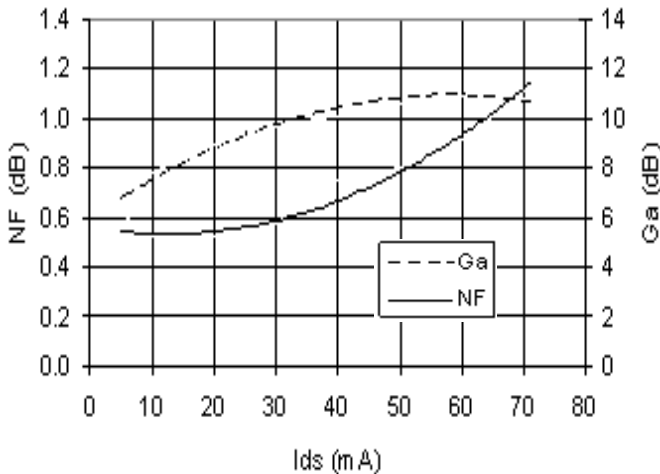
Gm & Ids vs. Vgs
Vds = 2.5V



NF & Associated Gain vs. Freq
Vds = 2.5V, Ids = 14mA



NF & Ga vs. Ids
Freq = 12GHz, Vds = 2.5V



DC IV Characteristics

